

Lab 11: MOSFET Amplifier Configurations

ECEN 325 - 511

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Date Performed: November 30, 2021

Due Date: December 7, 2021

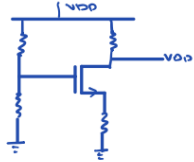
Purpose

The objective of this lab was to be able to analyze MOS amplifier configurations. Different factors for common-source and common-drain topologies are learned.

Calculations

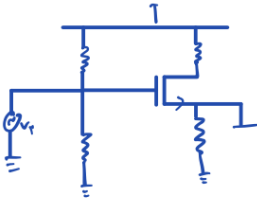
1)

DC & AC Analysis



$$V_G = \frac{V_{DD} \times R_{G2}}{R_{G1} + R_{G2}}$$

$$R_G = (R_{G1} \parallel R_{G2})$$



$$R_i \geq 10k\Omega$$

$$R_i = (R_{G1} \parallel R_{G2}) = R_G$$

$$\frac{R_{G1} \cdot R_{G2}}{R_{G1} + R_{G2}} \geq 10k\Omega$$

$$\text{so assume } R_i = 30k\Omega \geq 10k\Omega$$

$$R_{G1} = 40k\Omega \text{ \& } R_{G2} = 120k\Omega \text{ so } R_i = 30k\Omega$$

$$V_G = \frac{V_{DD} \times R_{G2}}{R_{G1} + R_{G2}} = \frac{5 \times 120k}{(40 + 120)k} = 5.75V$$

$$-V_G + V_{G1} + V_{G2} = 0$$

$$V_{G1} = V_G - V_{G2}$$

$$= 5.75 - 1$$

$$V_{G1} = 2.75$$

$$V_t = 1V$$

$$g_m = k \frac{W}{L}$$

$$k_n = \frac{1}{2} k_{n0} \frac{W}{L} = 1mA/V^2$$

$$I_{DS} = k_n (V_{G1} - V_t)^2 \Rightarrow I_{DS} = 3.0625mA$$

$$V_{DS} = 1V \quad R_D = 0.32k\Omega$$

$$A_v = 25$$

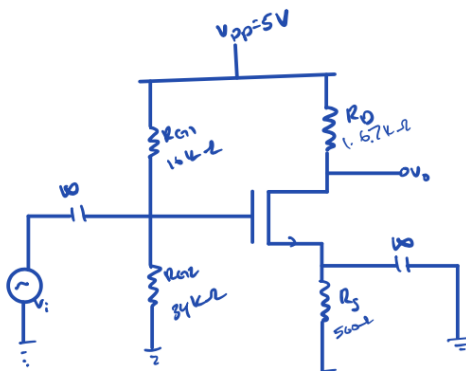
$$g_m = 2k_n (V_{G1} - V_t) = 2 \times 1 (2.75 - 1)$$

$$= 3.5$$

$$\text{gain} = |3.5 \times 10^{-3} \times R_D| = 25$$

$$R_D = 1.67k\Omega$$

Whole circuit :



$$0 \text{ to peak} \rightarrow V_o \geq 1V$$

$$|gain| V_i \geq 1V$$

$$25 \cdot 1 \geq 1V$$

$$V_i \geq \frac{1}{25} \Rightarrow V_i \geq 0.04V$$

$$V_i \geq 40mV$$

2)

$$R_i = R_{G1} \parallel R_{G2}$$

$$= 40k \parallel 120k = \frac{40k \times 120k}{40 + 120} = 30k\Omega$$

$$\text{to gate: } 1/g_m$$

$$R_{out} = R_3 \parallel 1/g_m = 320 \parallel 1/g_m$$

from 2N7000G datasheet

$$g_m = 100 \times 10^{-6} A/V$$

$$A_v = \frac{g_m R_3}{1 + g_m R_3}$$

$$= R_3 / \left(\frac{1}{g_m} + R_3 \right)$$

$$R_{out} = 320 \parallel 1/100 \times 10^{-6} = \frac{0.32k \times 10k}{0.32k + 10k} = 310.07\Omega$$

$$A_v = \frac{8 \cdot 520}{10k + 320} = 0.021$$

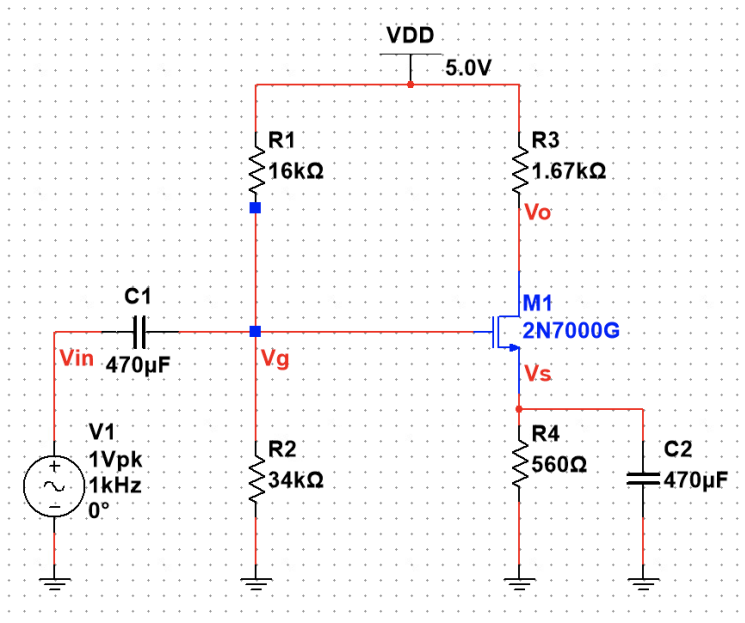
$$R_i = 30k\Omega$$

$$R_o = 310.07\Omega$$

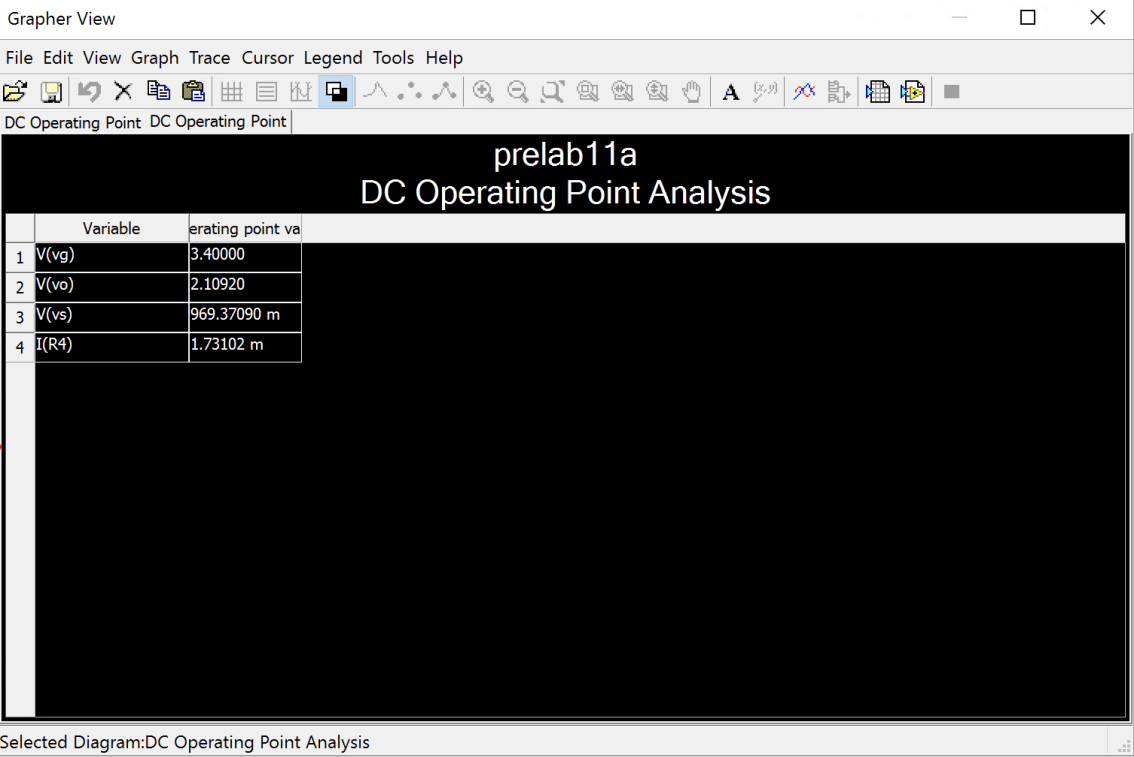
$$A_v = 0.021$$

Simulations (on Multisim)

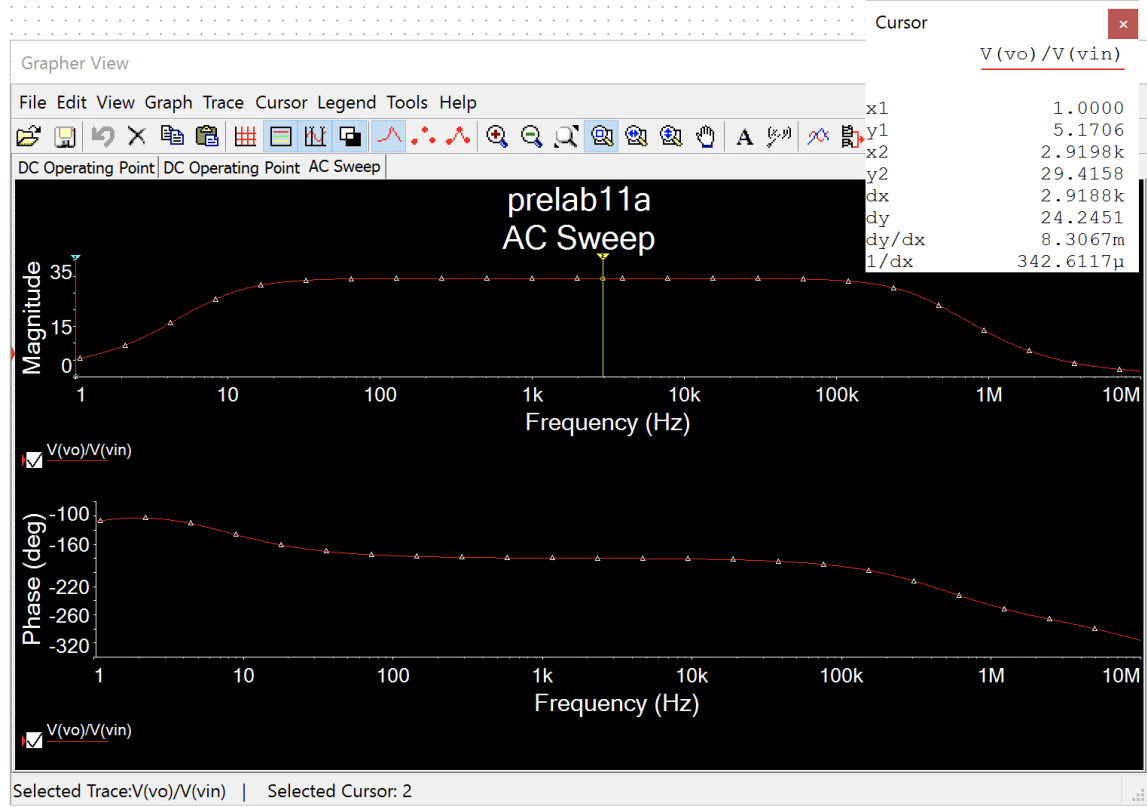
3a Schematic



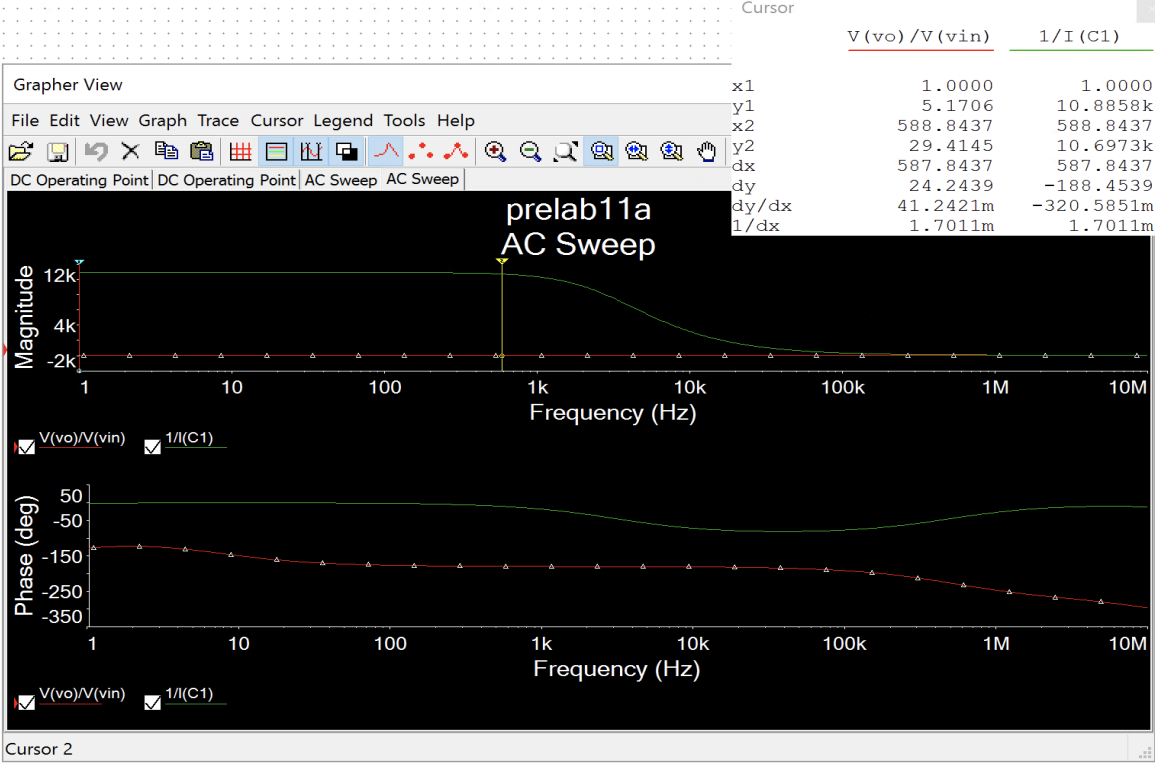
3a DC Operating point



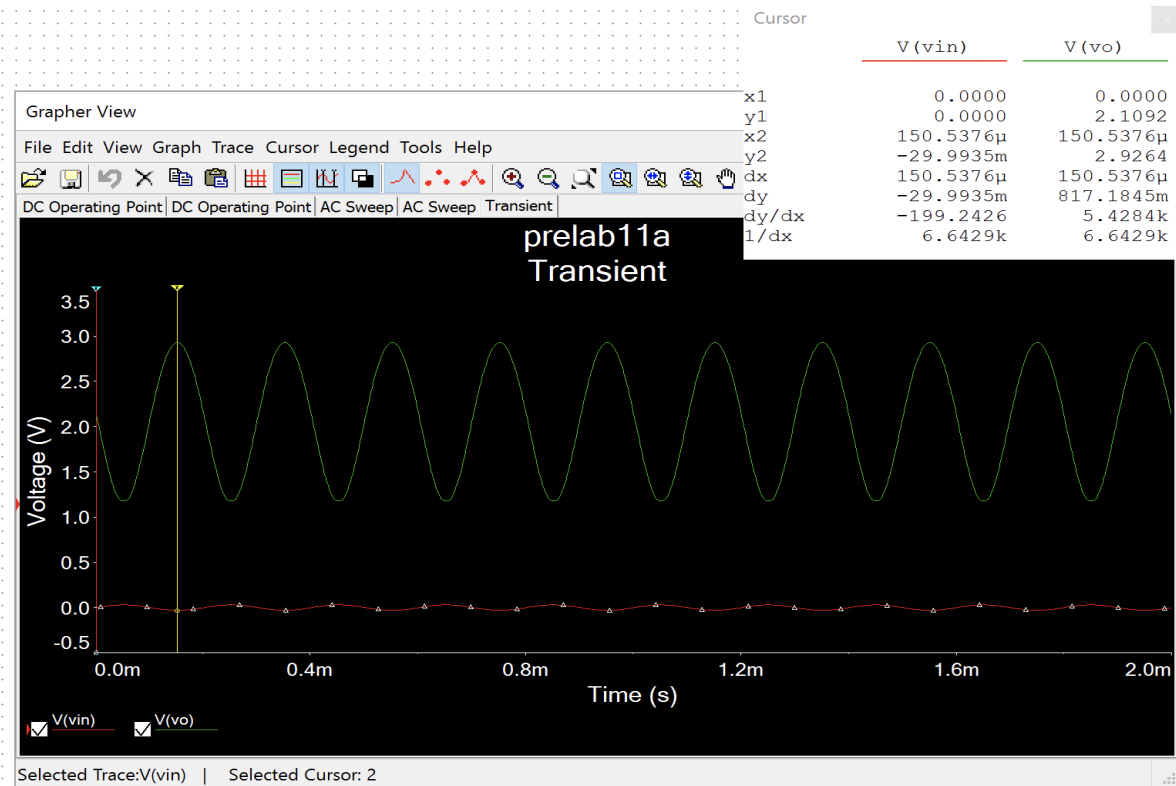
3a AC simulation A_v



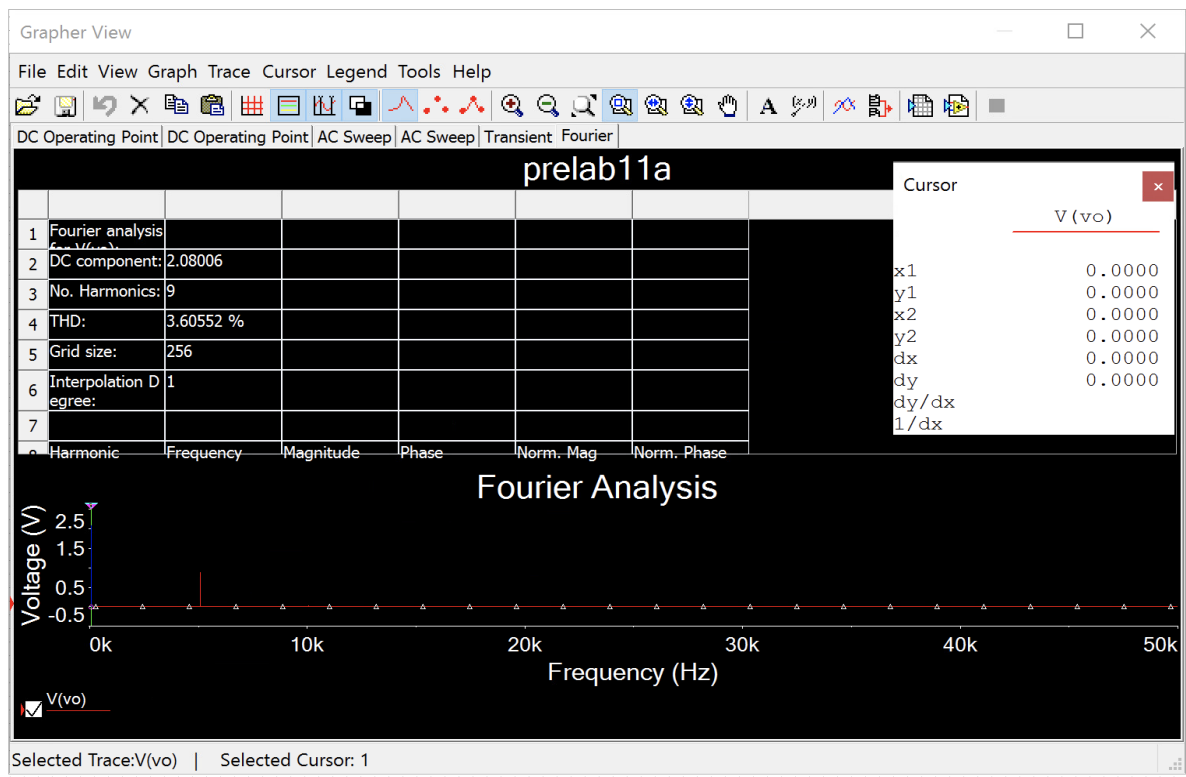
3a AC simulation R_i



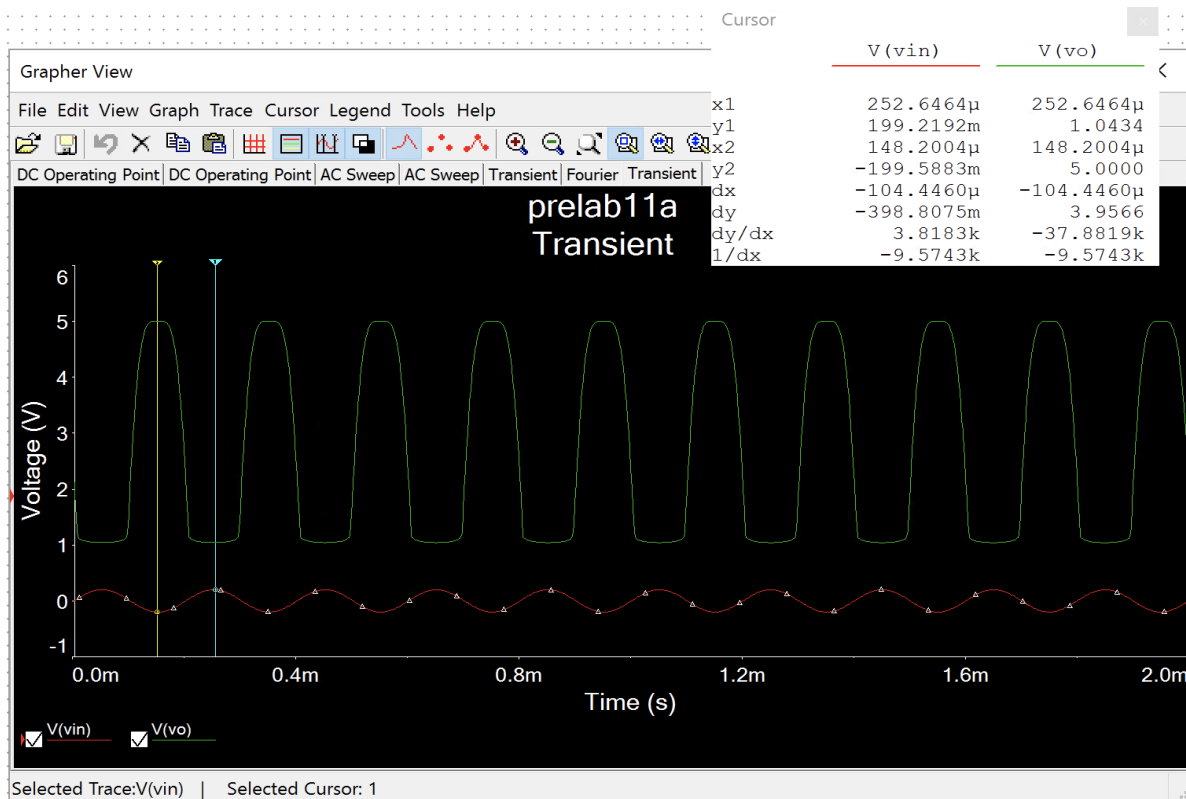
3a Transient



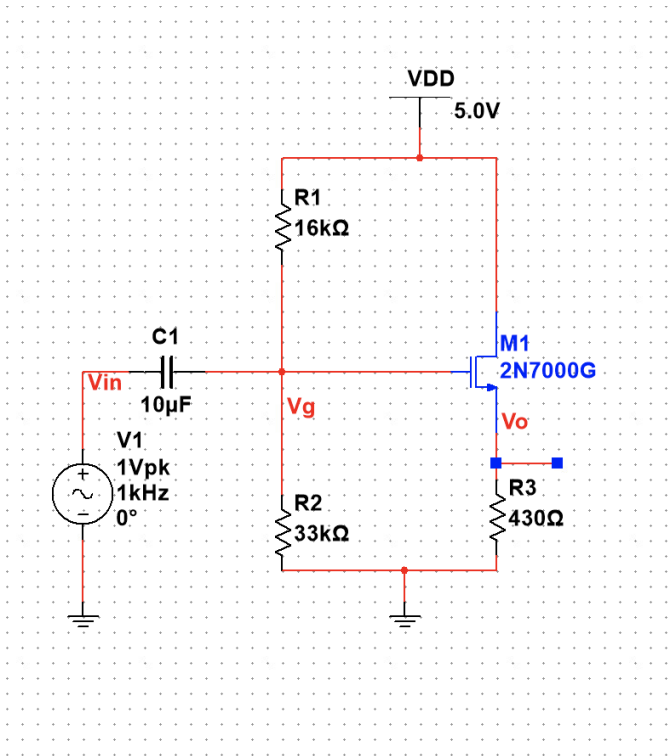
3a THD



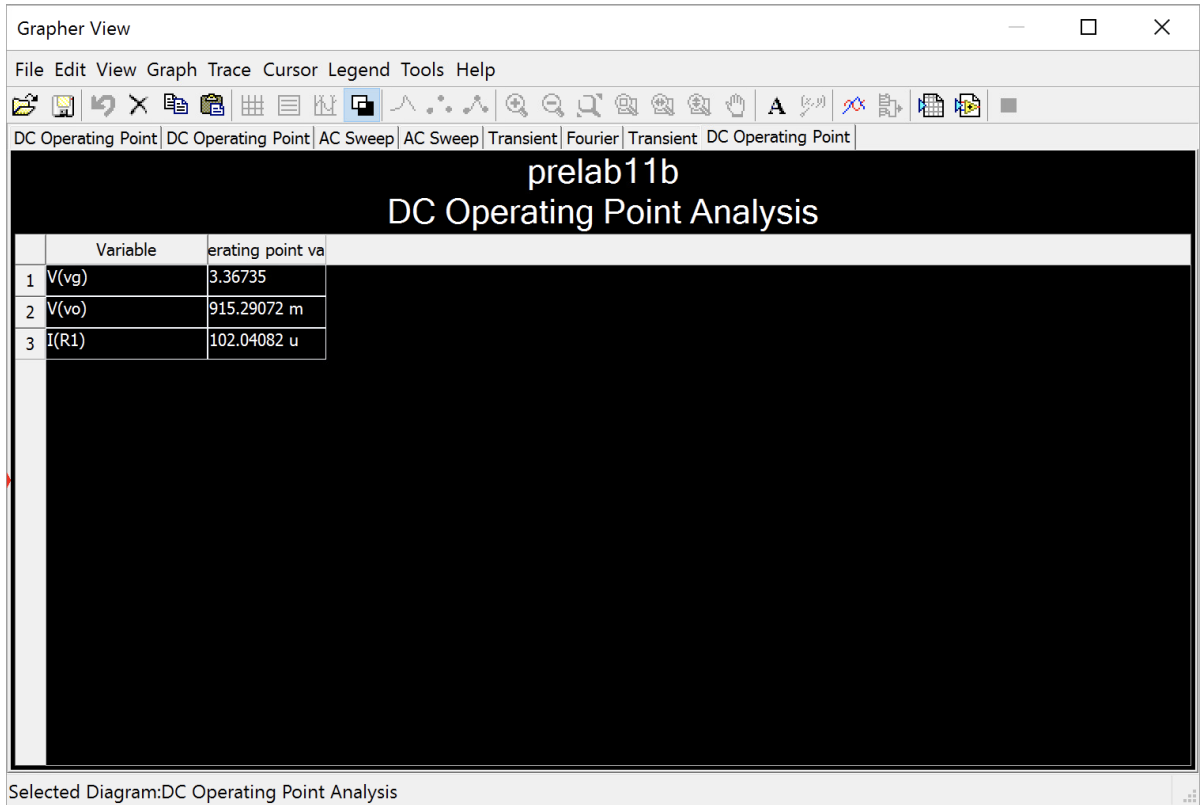
3a Clipping



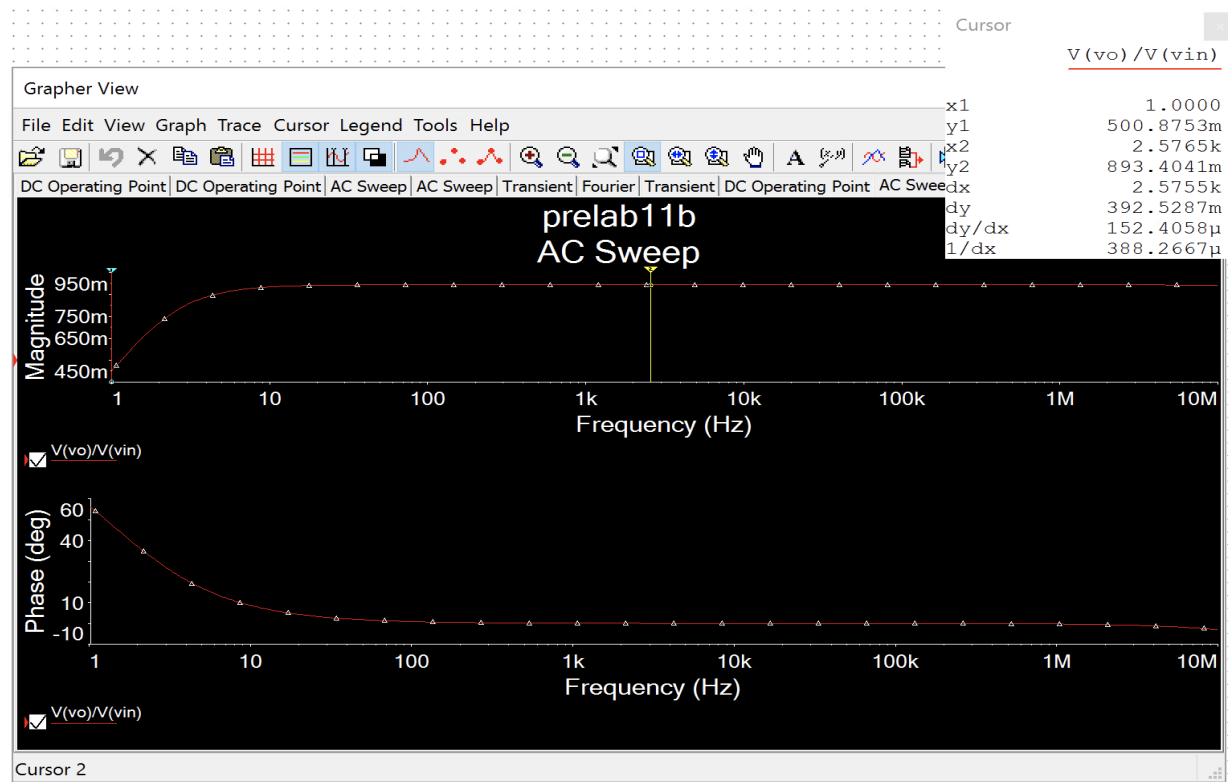
5a Schematic



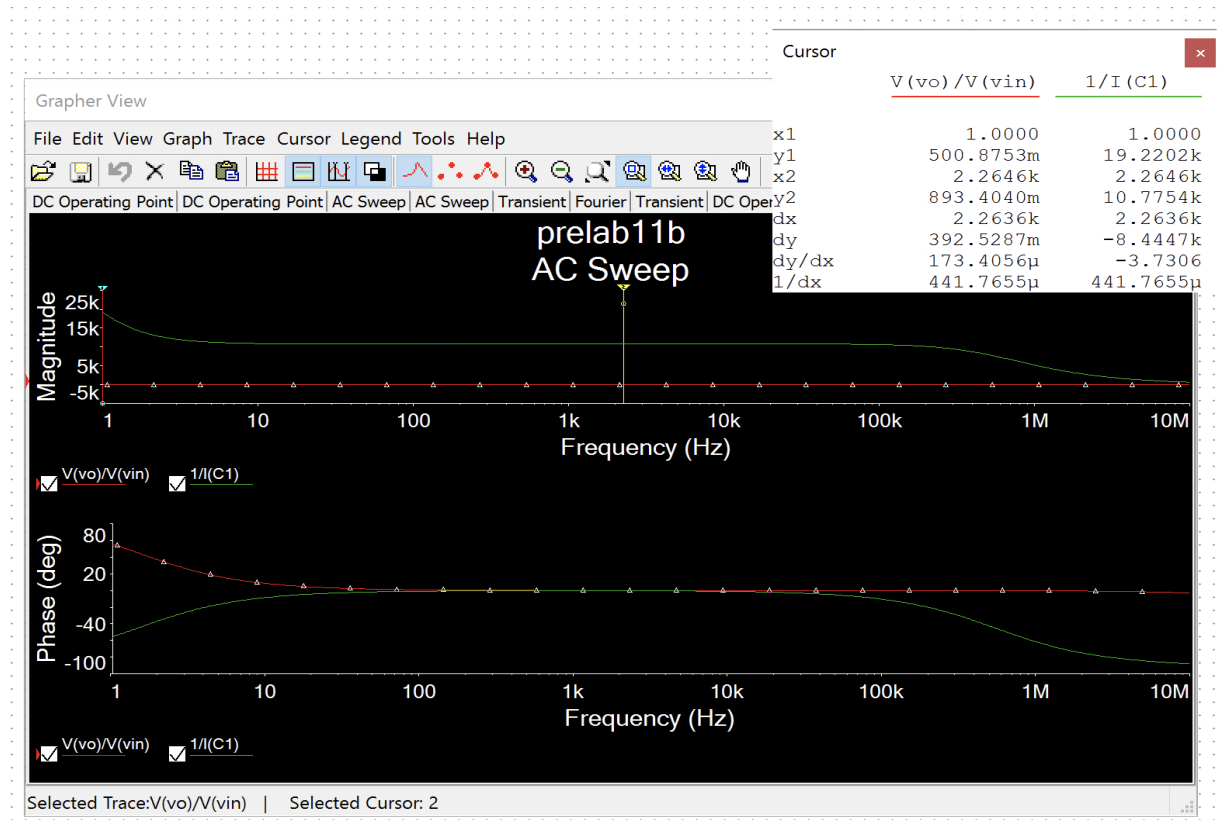
5a DC Operating point



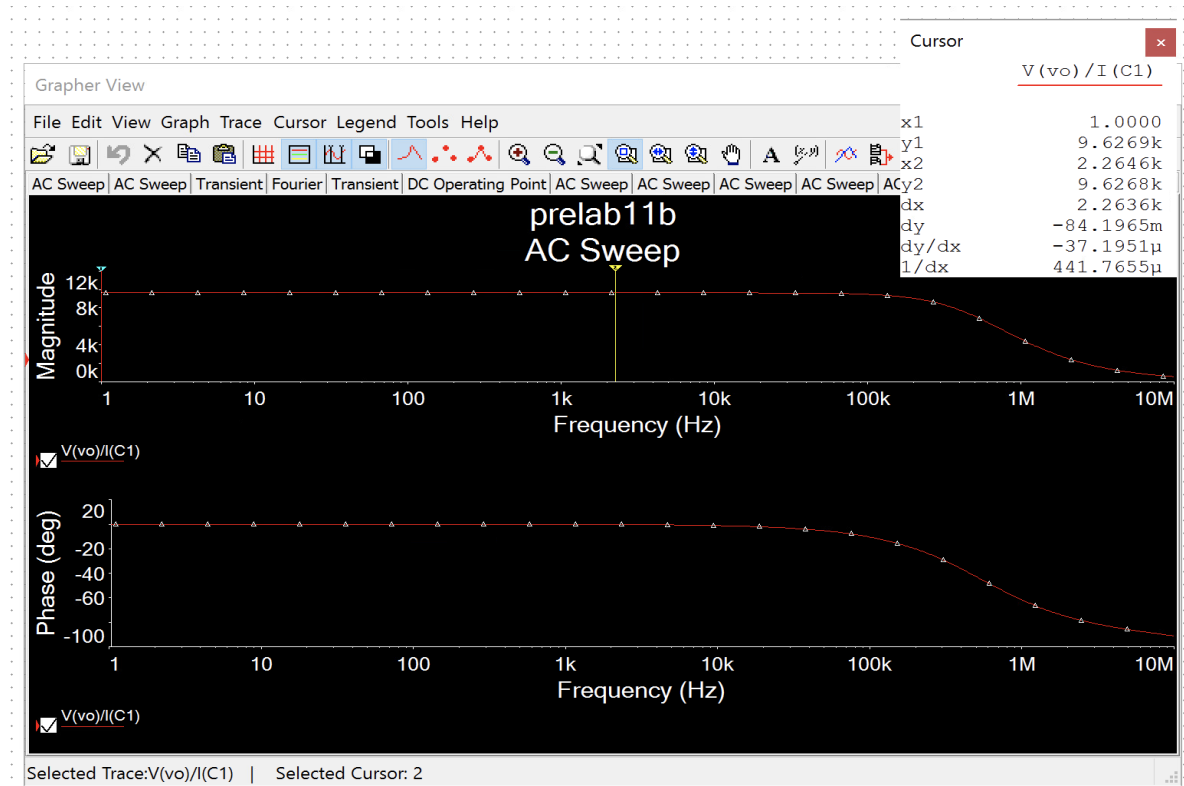
5a AC simulation A_v



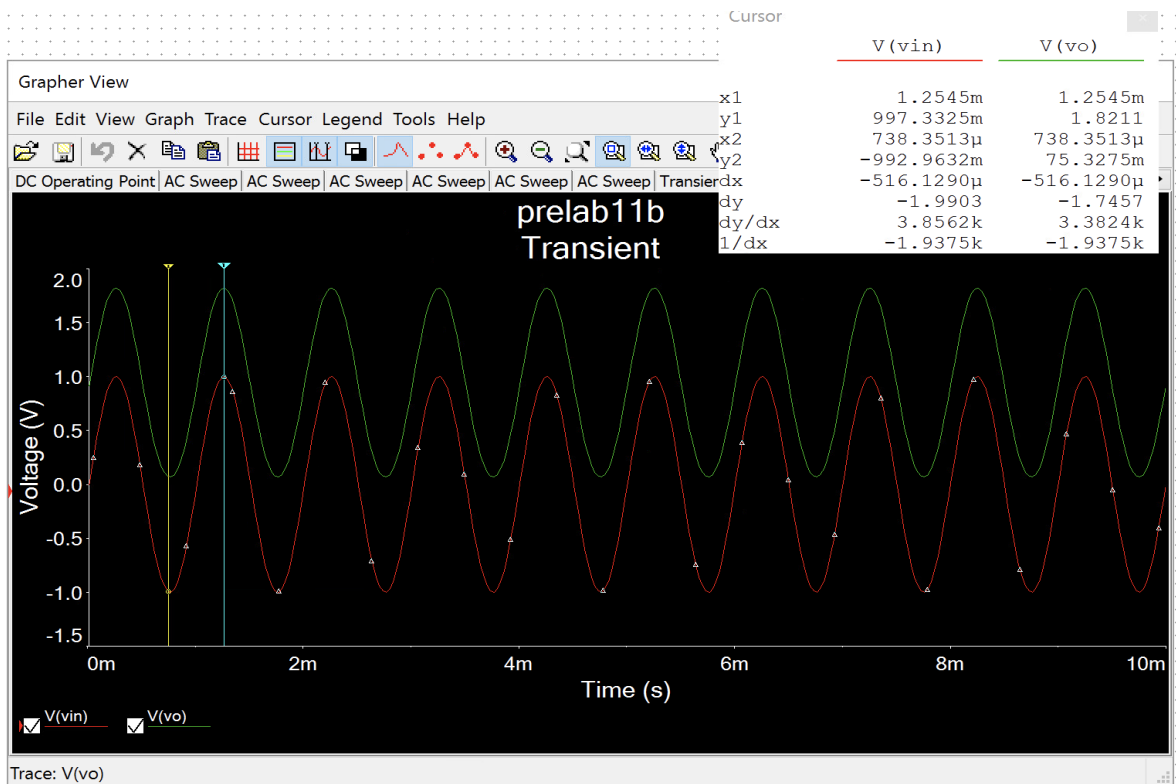
5a AC simulation R_i



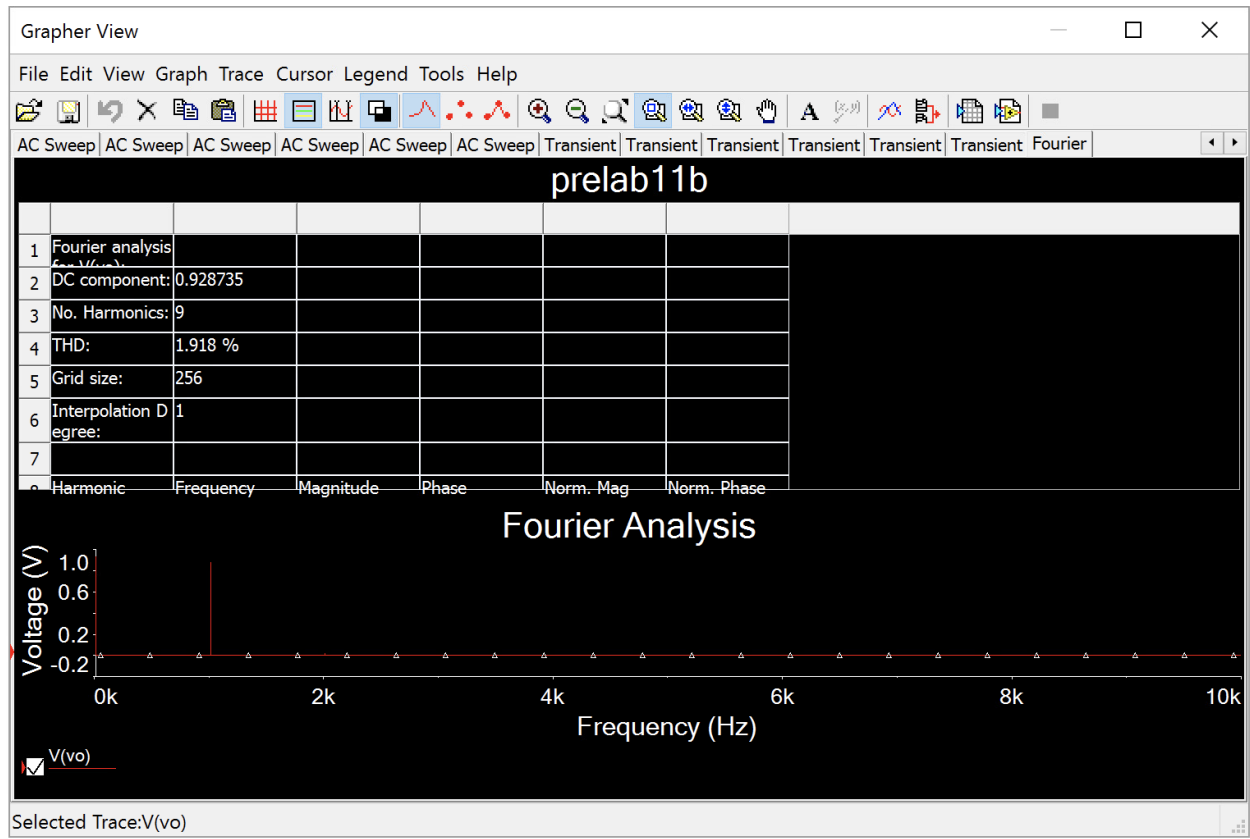
5a AC simulation R_o



5a Transient



5a THD

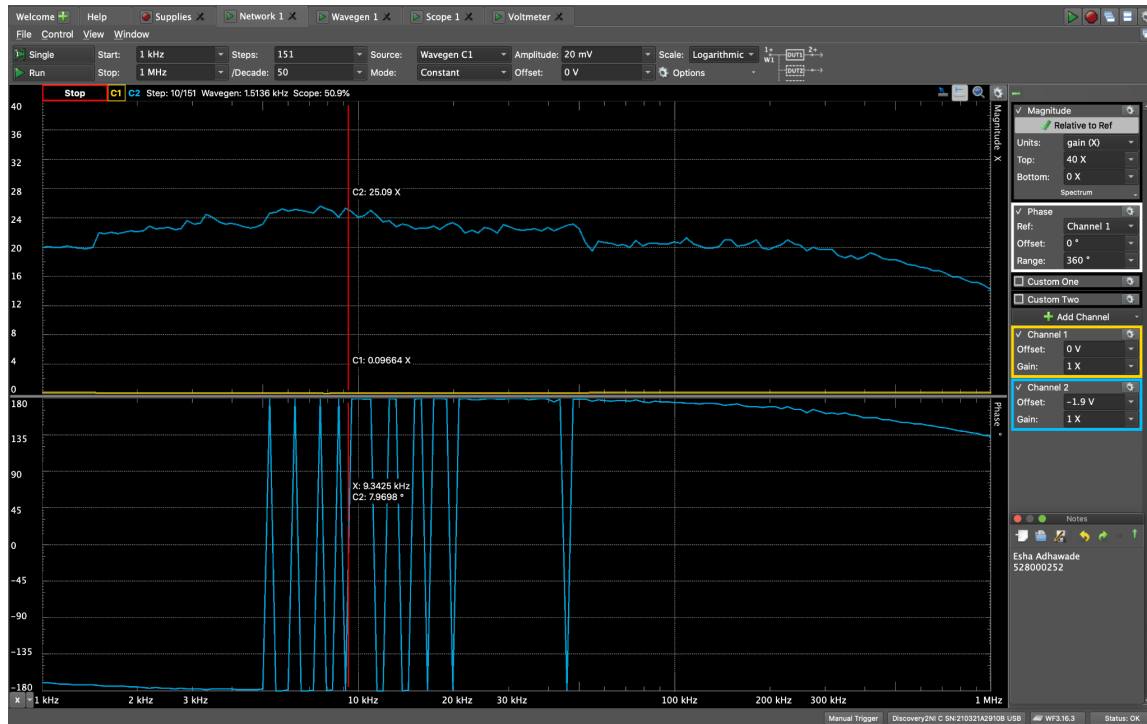


Measurements

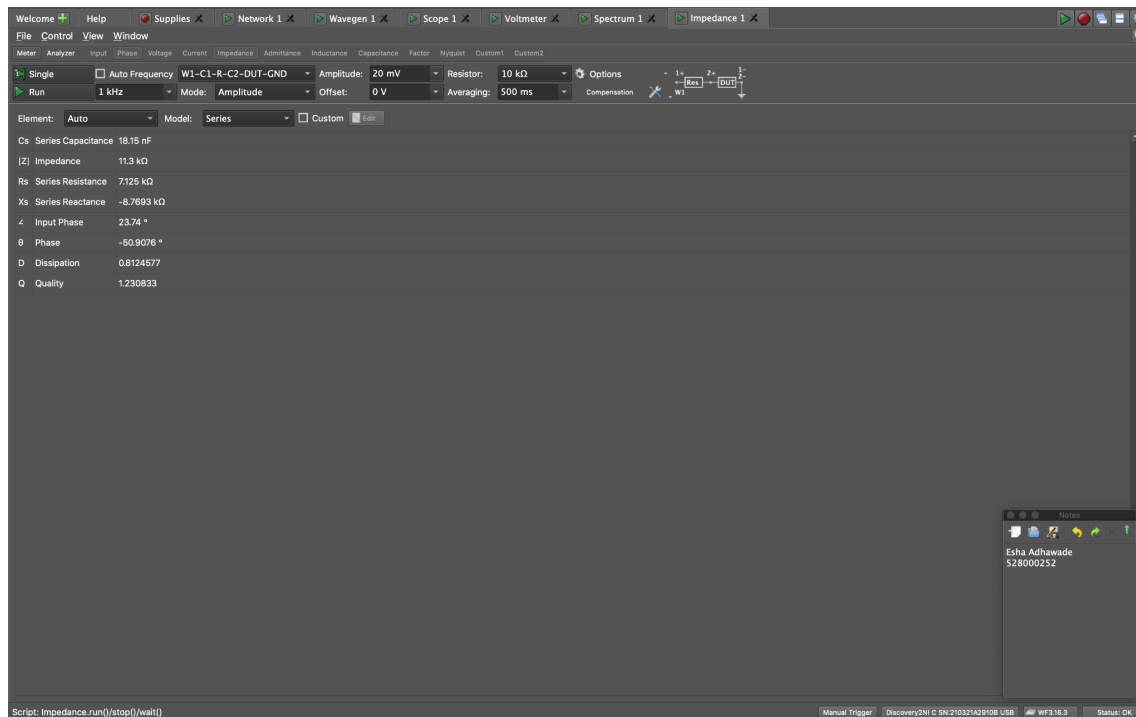
3a DC Values

In the Data Tables Section

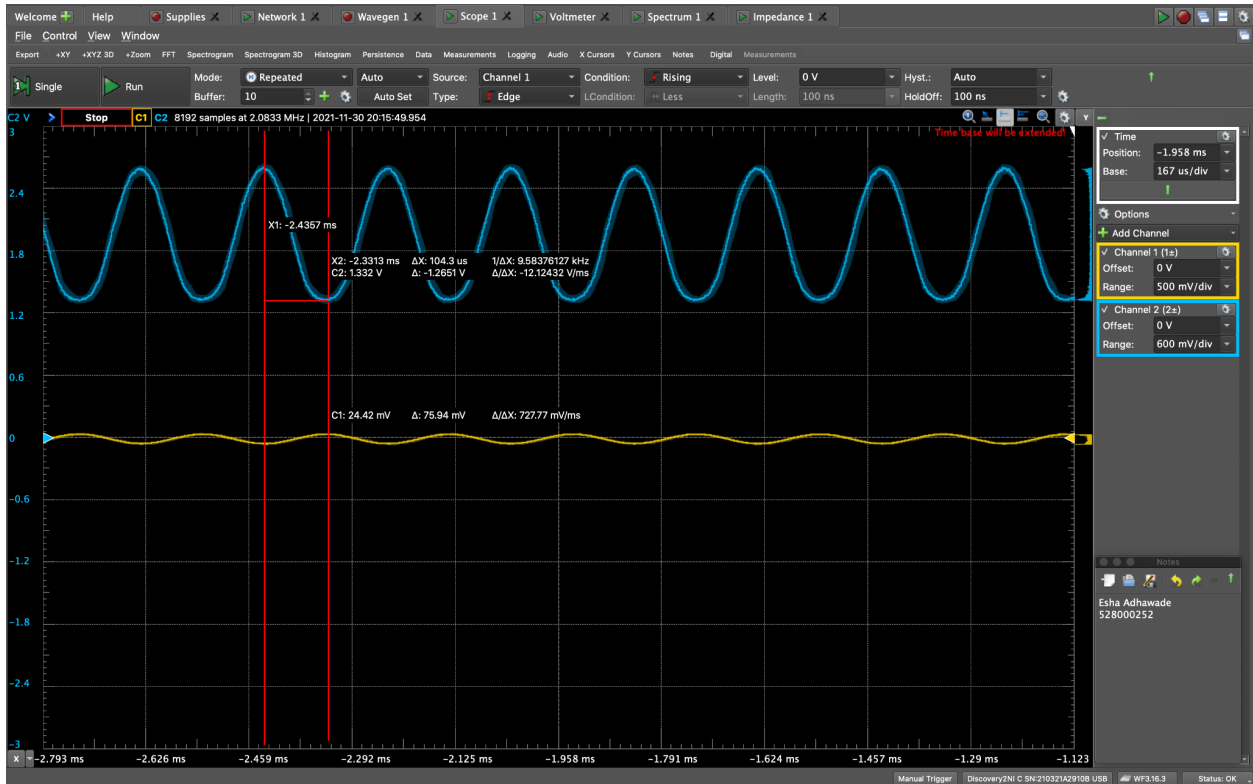
3a AC simulation A_v



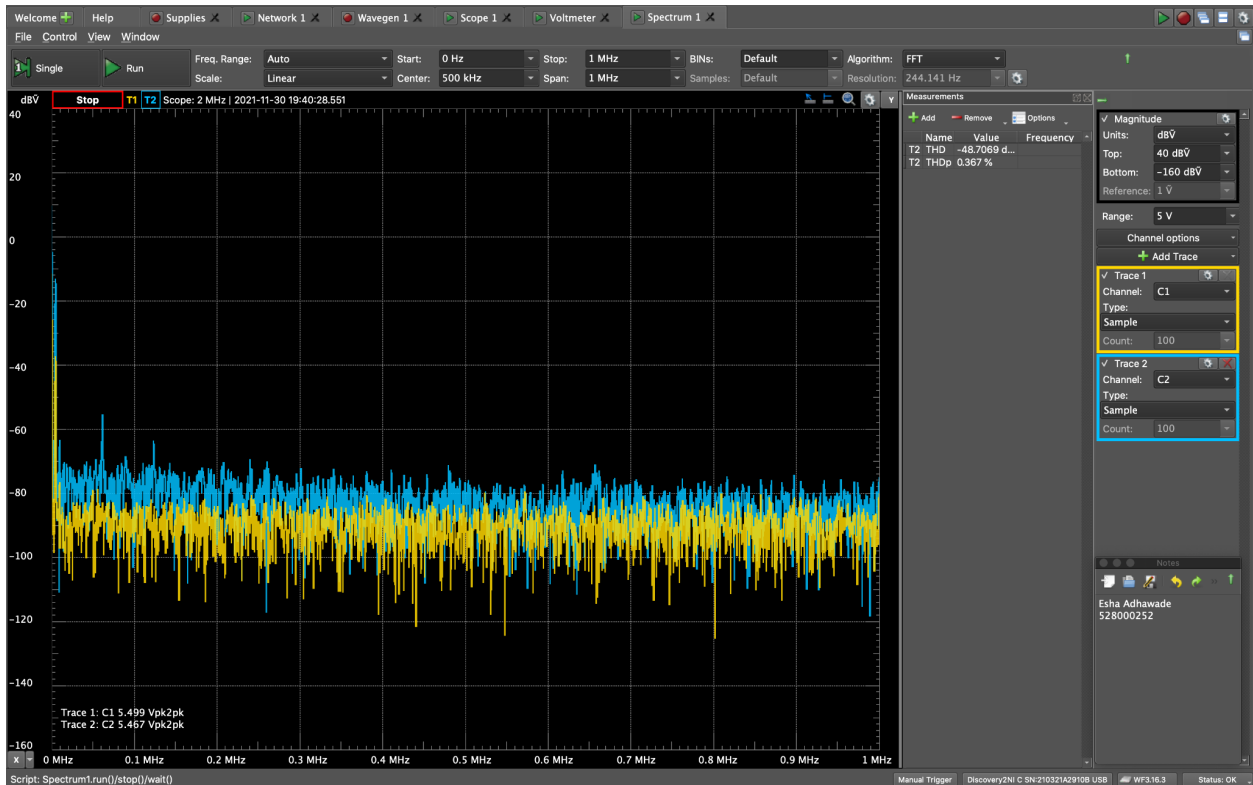
3a AC simulation R_i



3a Transient



3a THD

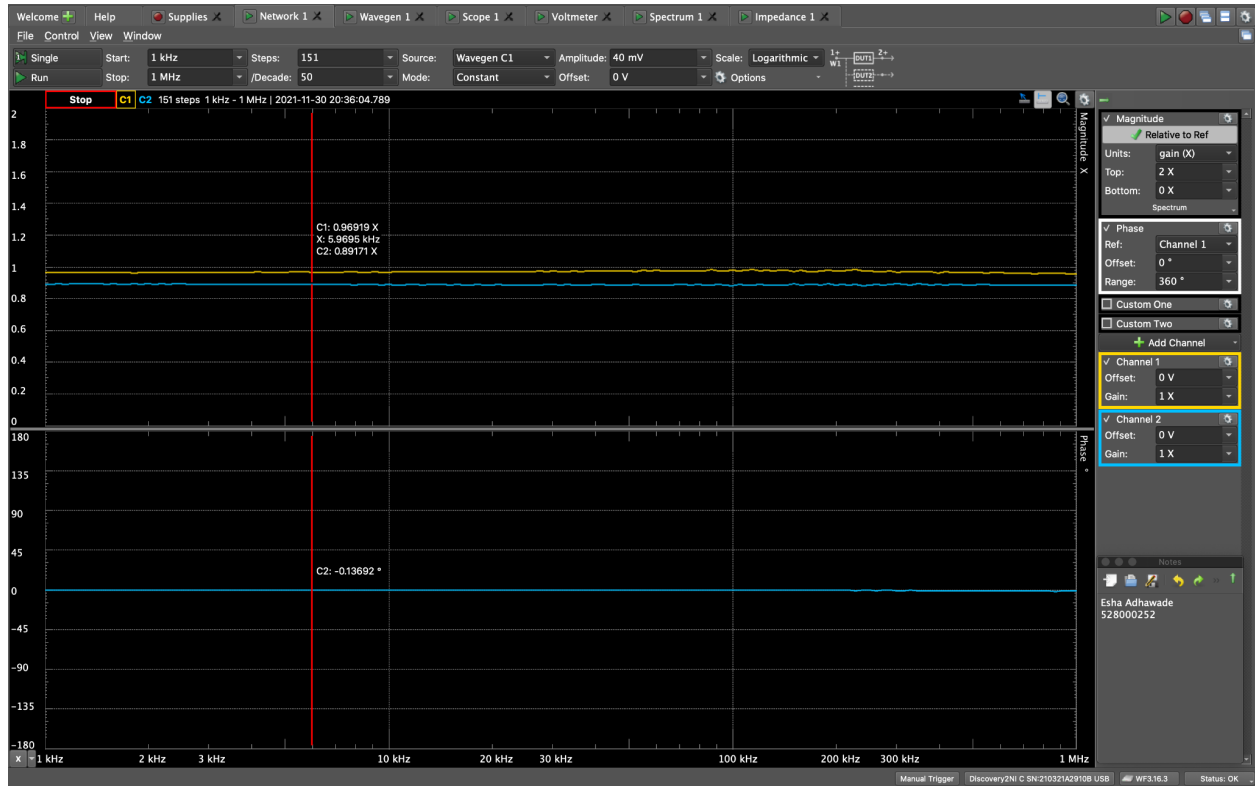


3a Clipping Point: 55 mV

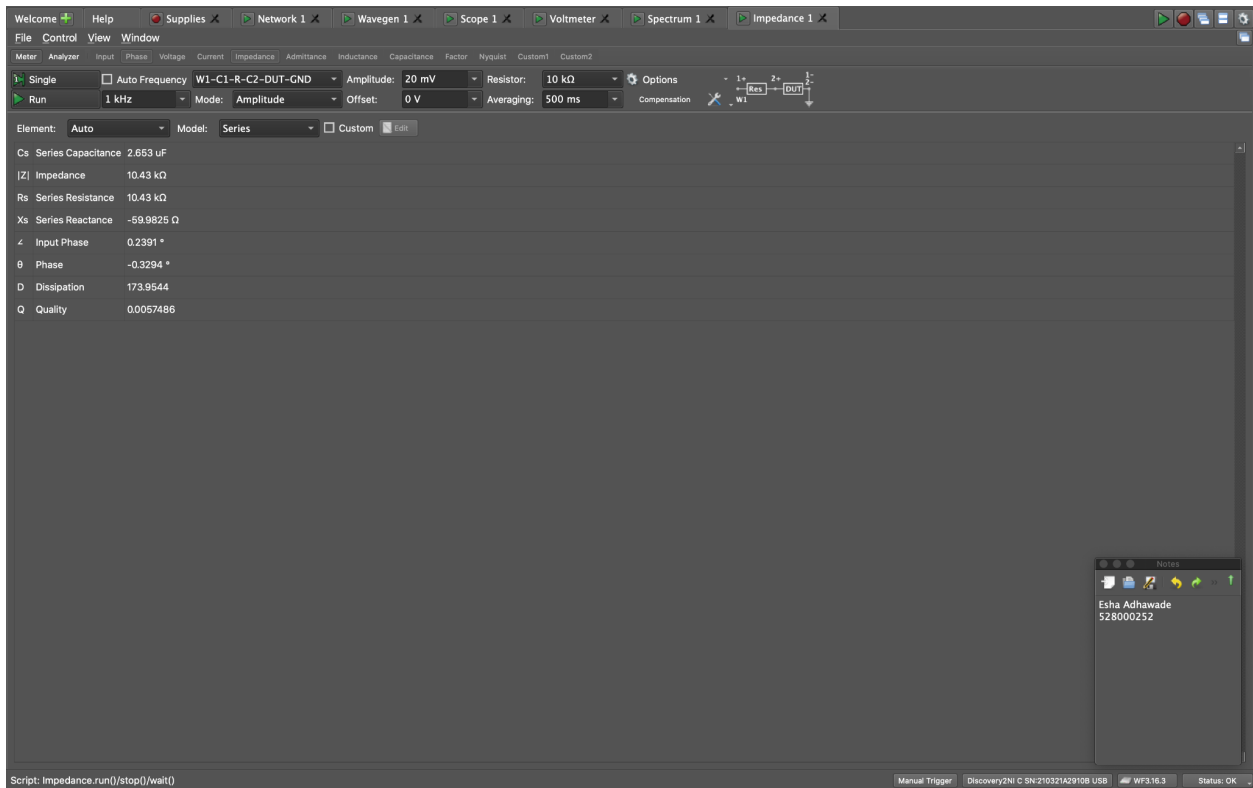
5a DC Values

In the Data Tables Section

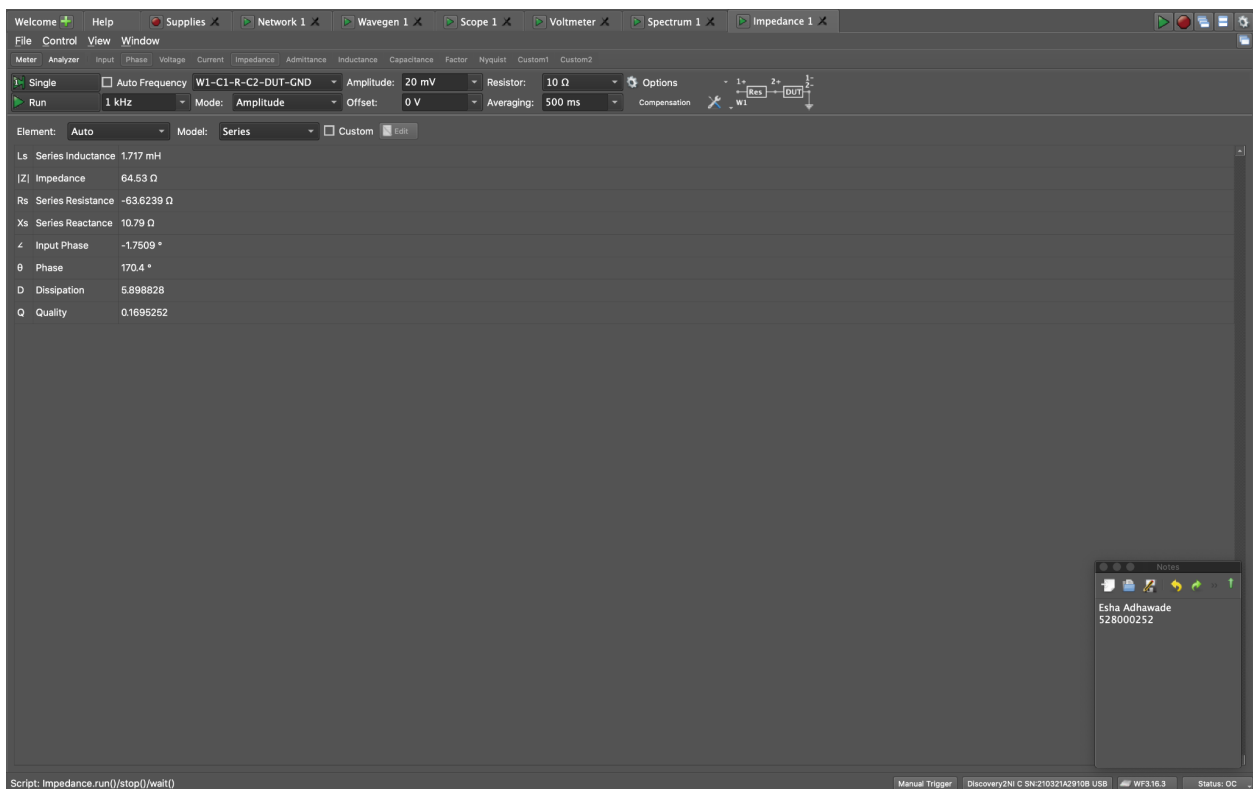
5a AC simulation A_v



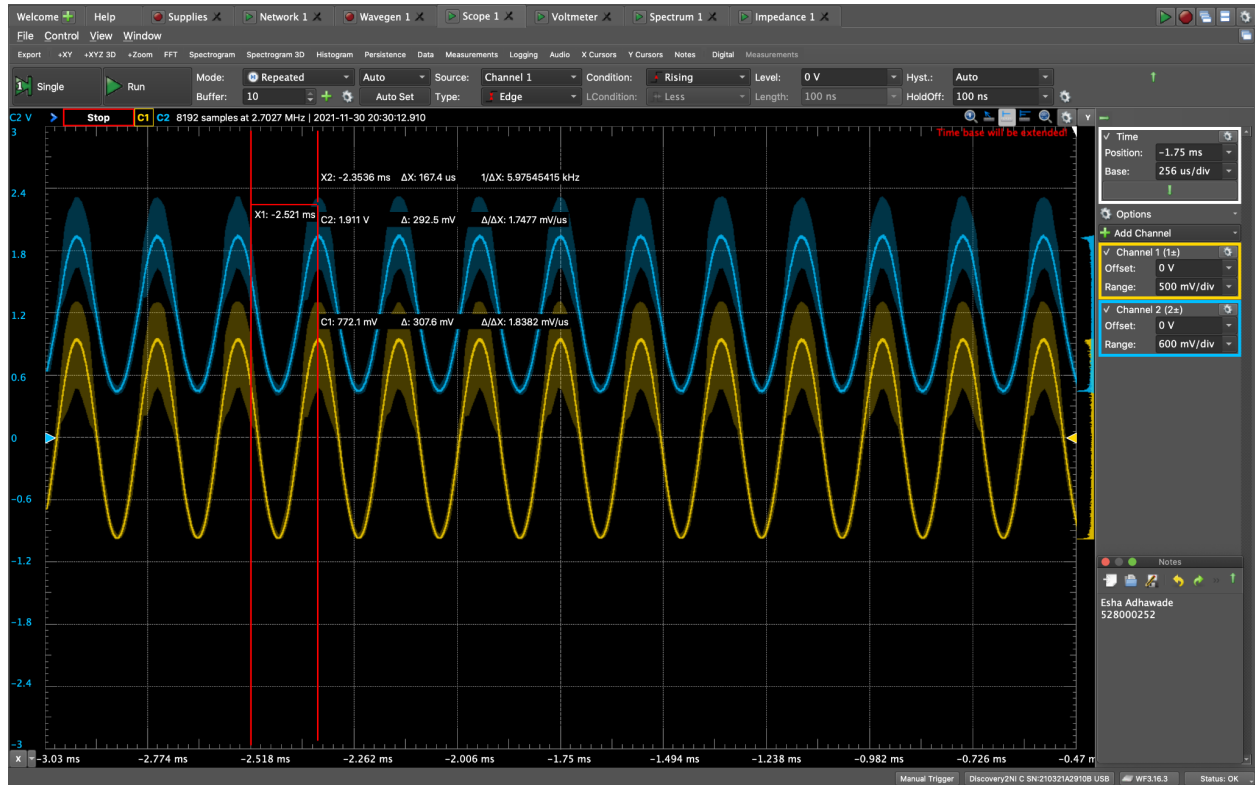
5a AC simulation R_i



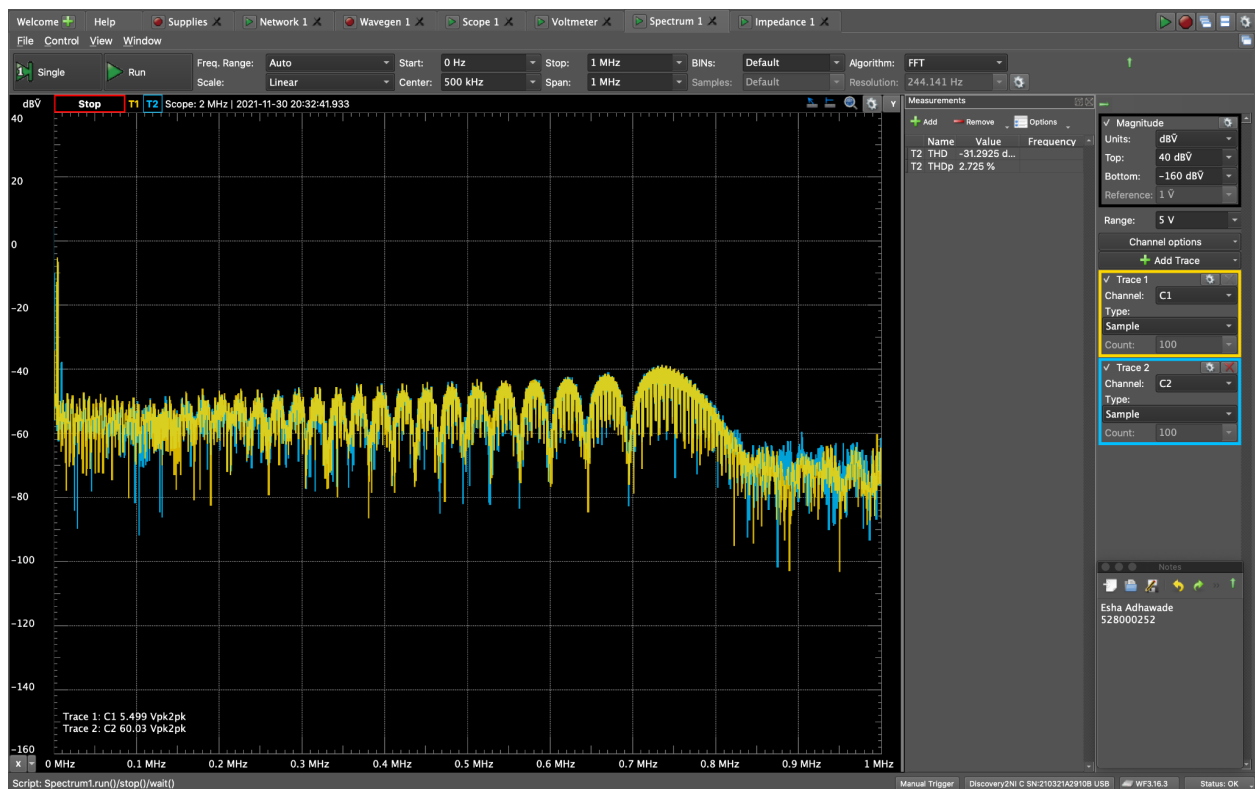
5a AC simulation R_o



5a Transient



5a THD



Data Tables**Figure 3**

DC Values

	Simulations	Measurements
V_{RG2}	3.4000 V	3.325 V
V_{RS}	969.37090 mV	1.0014 V
V_{RD}	1.934 V	2.076 V
$V_{o, dc}$	2.10920 V	2.0961 V
I_C	1.73102 mA	1.92013 mA

Other

	Calculations	Simulations	Measurements
A_v	25	29.415	25.09
R_i	10k	10.6973k	11.3k
THD	-	3.60552%	0.367%

Figure 5

DC Values

	Simulations	Measurements
V_{RG2}	3.36735	3.5667 V
V_{RS}	952.278 mV	1.0012 V
I_C	102.04082 μ A	1.0812 mA

Other

	Calculations	Simulations	Measurements
A_v	0.031	0.89340	0.89171
R_i	10k	10.7754k	10.43k
R_o	310.07	84.234	64.53
THD	-	1.918%	2.725%

Discussion

For lab 11, students learned to analyze MOS amplifier configurations. Most of the values between the simulations and measurements were pretty consistent for the circuits. If there were any minor differences, that's probably because of component differences, old breadboards, or loose wires. In this lab, I used slightly different resistor values in my measurements in comparison to simulations.